CMOS Digital Integrated Circuits Silicon Monolithic

74VHC9164FT

1. Functional Description

• 8-Bit Shift Register (P-IN, S-OUT/S-IN, P-OUT)

2. General

The 74VHC9164FT is an ultra-high-speed 8-Bit Shift Register fabricated using silicon-gate CMOS technology. The 74VHC9164FT combines low power consumption of CMOS with Schottky TTL speeds.

The 74VHC9164FT has parallel data inputs/outputs, a serial input and a serial output. It converts parallel data into serial data or vice versa.

When P/S CONT is Low, Q/D1 to Q/D8 are configured as parallel data outputs. At this time, the SI input is serially loaded on the rising edges of CK and unloaded from the Q/D1 to Q/D8 outputs in parallel. When $\overline{\text{CLR/LOAD}}$ input is Low, all flip-flops are asynchronously reset, irrespective of the CK state.

When P/S CONT is High, Q/D1 to Q/D8 are configured as parallel data inputs. At this time, when $\overline{\text{CLR/LOAD}}$ is Low, Q/D1 to Q/D8 latch data in parallel asynchronously from the CK input.

All the inputs have hysteresis between the positive-going and negative-going thresholds. Thus the 74VHC9164FT is capable of squaring up transitions of slowly changing input signals and provides an improved noise immunity. Additionally, all the inputs have a newly developed protection circuit without a diode returned to V_{CC} . This enables the inputs to be tolerant of up to 5.5 volts even when power supply is down.

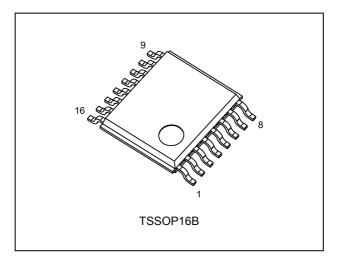
The input power-down protection capability makes the 74VHC9164FT ideal for a wide range of applications, such as interfacing between different voltages, voltage translation from 5 V to 3 V and battery back-up circuits.

3. Features

- (1) AEC-Q100 (Rev. H) (Note 1)
- (2) Wide operating temperature range: $T_{opr} = -40$ to 125 °C
- (3) High speed: $f_{MAX} = 149 \text{ MHz}$ (typ.) at $V_{CC} = 5.0 \text{ V}$
- (4) Low power dissipation: $I_{CC} = 4.0 \mu A$ (max) at $T_a = 25 \, ^{\circ}C$
- (5) Power-down protection is provided on all inputs.
- (6) Balanced propagation delays: t_{PLH} ≈ t_{PHL}
- (7) Wide operating voltage range: $V_{CC(opr)} = 2.0 \text{ V}$ to 5.5 V

Note 1: This device is compliant with the reliability requirements of AEC-Q100. For details, contact your Toshiba sales representative.

4. Packaging

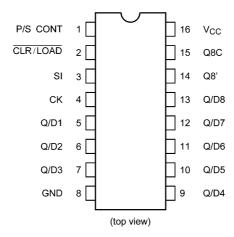


Start of commercial production

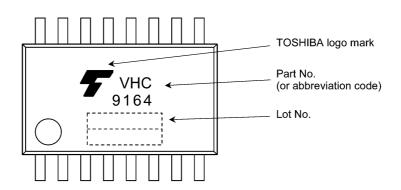
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5. Pin Assignment



6. Marking



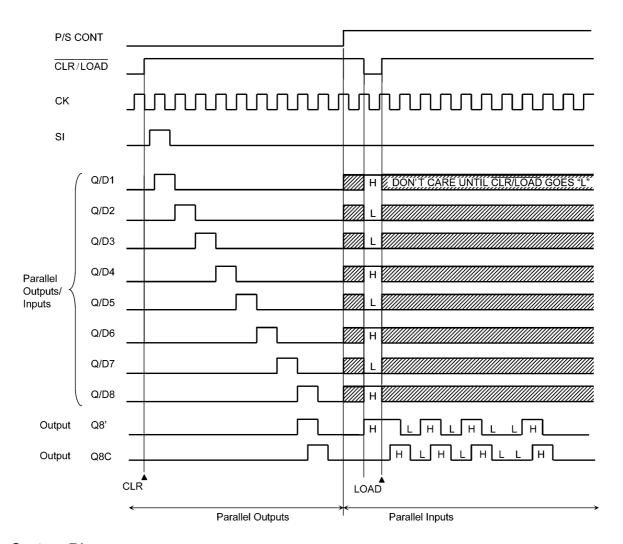
7. Truth Table

	Inputs Parallel Outputs/Inputs				Function
P/S CONT	CLR/LOAD	SI	СК	Q/D1·····Q/D8	
L	Х	Х	Х		Q/D1 to Q/D8 are configured as parallel outputs.
L	L	Х	Х		Shift register is cleared.
L	Н	L		Output- state	First stage of S.R. becomes "L". Other stages store the data of previous stage, respectively.
L	Н	Н			First stage of S.R. becomes "H". Other stages store the data of previous stage, respectively.
L	Н	Х	—		The shift register remains unchanged. The Q8C output keeps the value of the previous flip-flop.
Н	Х	Х	Х		Q/D1 to Q/D8 are configured as parallel inputs.
Н	L	Х	Х		Q/D1 to Q/D8 are latched into the shift register.
Н	Н	٦		Input- state	First stage of S.R. becomes "L". Other stages store the data of previous stage, respectively.
Н	Н	Н		Parallel Inputs	First stage of S.R. becomes "H". Other stages store the data of previous stage, respectively.
Н	Н	Х			The shift register remains unchanged. The Q8C output keeps the value of the previous flip-flop.

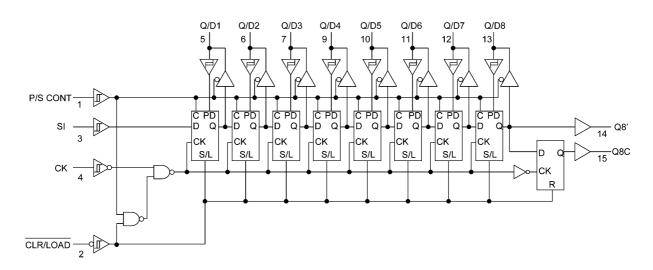
X: Don't care



8. Timing Diagrams



9. System Diagram





10. Absolute Maximum Ratings (Note)

Characteristics	Symbol	Note	Rating	Unit
Supply voltage	V _{CC}		-0.5 to 7.0	V
Input voltage	V _{IN}		-0.5 to 7.0	V
Output voltage	V _{OUT}		-0.5 to V _{CC} + 0.5	V
Bus I/O voltage	V _{I/O}	(Note 1)	-0.5 to 7.0	V
(Q/D1 to Q/D8)		(Note 2)	-0.5 to V _{CC} + 0.5	
Input diode current	I _{IK}		-20	mA
Output diode current	I _{OK}		±20	mA
Output current	I _{OUT}		±25	mA
V _{CC} /ground current	I _{CC}		±75	mA
Power dissipation	P _D	(Note 3)	180	mW
Storage temperature	T _{stg}		-65 to 150	°C

Note: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Output in OFF state.

Note 2: High (H) or Low (L) state. I_{OUT} absolute maximum rating must be observed.

Note 3: 180 mW in the range of T_a = -40 to 85 °C. From T_a = 85 to 125 °C a derating factor of -3.25 mW/°C shall be applied until 50 mW.

11. Operating Ranges (Note)

Characteristics	Symbol	Note	Rating	Unit
Supply voltage	V _{CC}		2.0 to 5.5	V
Input voltage	V _{IN}		0 to 5.5	V
Output voltage	V _{OUT}		0 to V _{CC}	V
Bus I/O voltage	V _{I/O}	(Note 1)	0 to 5.5	V
(Q/D1 to Q/D8)		(Note 2)	0 to V _{CC}	
Operating temperature	T _{opr}		-40 to 125	$^{\circ}$

Note: The operating ranges must be maintained to ensure the normal operation of the device.

Unused inputs must be tied to either V_{CC} or GND.

Note 1: Output in OFF state.

Note 2: High (H) or Low (L) state.



12. Electrical Characteristics

12.1. DC Characteristics (Unless otherwise specified, T_a = 25 °C)

Characteristics	Symbol	Test Condition		V _{CC} (V)	Min	Тур.	Max	Unit
Positive threshold voltage	V _P	_		3.0	_	_	2.20	V
				4.5	_	_	3.15	
				5.5	_	_	3.85	
Negative threshold voltage	V _N	_		3.0	0.90	_	_	V
				4.5	1.35	_	_	
				5.5	1.65	_	_	
Hysteresis voltage	V _H	_		3.0	0.30		1.20	V
				4.5	0.40	_	1.40	
				5.5	0.50	_	1.60	
High-level output voltage V _{OH}		V _{IN} = V _{IH} or V _{IL}	I _{OH} = -50 μA	2.0	1.9	2.0	_	V
				3.0	2.9	3.0	_	
				4.5	4.4	4.5	_	
			I _{OH} = -4 mA	3.0	2.58		_	
			I_{OH} = -8 mA	4.5	3.94		_	
Low-level output voltage	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 50 μA	2.0	_	0.0	0.1	V
				3.0	_	0.0	0.1	
				4.5	_	0.0	0.1	
			I _{OL} = 4 mA	3.0	_		0.36	
			I _{OL} = 8 mA	4.5	_	_	0.36	
3-state output OFF-state leakage current (Q/D1 to Q/D8)	I _{OZ}	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{I/O} = 5.5 \text{ V or GND}$		0 to 5.5	_		±0.25	μА
Input leakage current	I _{IN}	V _{IN} = 5.5 V or GND		0 to 5.5			±0.1	μА
Quiescent supply current	Icc	$V_{IN} = V_{CC}$ or GND		5.5	_	_	4.0	μА

Rev.2.0



12.2. DC Characteristics (Unless otherwise specified, T_a = -40 to 85 °C)

Characteristics	Symbol	Test Condi	tion	V _{CC} (V)	Min	Max	Unit
Positive threshold voltage	V_P	_		3.0	_	2.20	V
				4.5	_	3.15	
				5.5	_	3.85	
Negative threshold voltage	V _N	_		3.0	0.90	_	V
				4.5	1.35	_	
				5.5	1.65	_	
Hysteresis voltage	V _H —			3.0	0.30	1.20	V
				4.5	0.40	1.40	
				5.5	0.50	1.60	
High-level output voltage	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -50 μA	2.0	1.9	_	V
				3.0	2.9	_	
				4.5	4.4	_	
			I _{OH} = -4 mA	3.0	2.48	_	
			I_{OH} = -8 mA	4.5	3.80	_	
Low-level output voltage	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 50 μA	2.0	_	0.1	V
				3.0	_	0.1	
				4.5	_	0.1	
			I _{OL} = 4 mA	3.0	_	0.44	
			I _{OL} = 8 mA	4.5	_	0.44	
3-state output OFF-state leakage current (Q/D1 to Q/D8)	I _{OZ}	$V_{IN} = V_{IH}$ or V_{IL} $V_{I/O} = 5.5 \text{ V or GND}$		0 to 5.5	_	±2.5	μА
Input leakage current	I _{IN}	V _{IN} = 5.5 V or GND		0 to 5.5		±1.0	μА
Quiescent supply current	I _{CC}	V _{IN} = V _{CC} or GND		5.5		40.0	μА



12.3. DC Characteristics (Unless otherwise specified, T_a = -40 to 125 °C)

Characteristics	Symbol	Test Condi	tion	V _{CC} (V)	Min	Max	Unit
Positive threshold voltage	V_P	_		3.0	_	2.20	V
				4.5	_	3.15	
				5.5	_	3.85	
Negative threshold voltage	V _N	_		3.0	0.90	_	V
				4.5	1.35	_	
				5.5	1.65	_	
Hysteresis voltage	V _H	_		3.0	0.30	1.20	V
				4.5	0.40	1.40	
				5.5	0.50	1.60	
High-level output voltage	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -50 μA	2.0	1.9	_	V
				3.0	2.9	_	
				4.5	4.4	_	
			$I_{OH} = -4 \text{ mA}$	3.0	2.40	_	
			I_{OH} = -8 mA	4.5	3.70	_	
Low-level output voltage	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 50 μA	2.0	_	0.1	V
				3.0	_	0.1	
				4.5	_	0.1	
			I _{OL} = 4 mA	3.0	_	0.55	
			I _{OL} = 8 mA	4.5	_	0.55	
3-state output OFF-state leakage current (Q/D1 to Q/D8)	I _{OZ}	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{I/O} = 5.5 \text{ V or GND}$		0 to 5.5	ı	±10.0	μА
Input leakage current	I _{IN}	V _{IN} = 5.5 V or GND		0 to 5.5		±2.0	μА
Quiescent supply current	I _{CC}	V _{IN} = V _{CC} or GND		5.5		80.0	μА

Rev.2.0



12.4. Timing Requirements (Unless otherwise specified, $T_a = 25$ °C, Input: $t_f = t_f = 3$ ns)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Limit	Unit
Minimum pulse width	$t_{w(L)}, t_{w(H)}$	_	3.3 ± 0.3	7.0	ns
(CK)			5.0 ± 0.5	5.0	
Minimum pulse width	t _{w(L)}	_	3.3 ± 0.3	6.0	ns
(CLR/LOAD)			5.0 ± 0.5	5.0	
Minimum setup time	t _S	_	3.3 ± 0.3	6.0	ns
(Q/D1 to Q/D8 -CLR/LOAD)			5.0 ± 0.5	5.0	
Minimum setup time	t _S	_	3.3 ± 0.3	6.0	ns
(SI-CK)			5.0 ± 0.5	5.0	
Minimum hold time	t _h	_	3.3 ± 0.3	1.0	ns
(Q/D1 to Q/D8 -CLR/LOAD)			5.0 ± 0.5	1.0	
Minimum hold time	t _h	_	3.3 ± 0.3	1.0	ns
(SI-CK)			5.0 ± 0.5	1.5	
Minimum removal time	t _{rem}	_	3.3 ± 0.3	5.0	ns
(CLR/LOAD-CK)			5.0 ± 0.5	3.0	

12.5. Timing Requirements (Unless otherwise specified, T_a = -40 to 85 °C, Input: t_r = t_f = 3 ns)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Limit	Unit
Minimum pulse width	$t_{w(L)}, t_{w(H)}$	_	3.3 ± 0.3	8.0	ns
(CK)			5.0 ± 0.5	6.0	
Minimum pulse width	t _{w(L)}	_	3.3 ± 0.3	7.0	ns
(CLR/LOAD)			5.0 ± 0.5	6.0	
Minimum setup time	t _S	_	3.3 ± 0.3	7.0	ns
(Q/D1 to Q/D8 -CLR/LOAD)			5.0 ± 0.5	6.0	
Minimum setup time	t _S	_	3.3 ± 0.3	7.0	ns
(SI-CK)			5.0 ± 0.5	5.0	
Minimum hold time	t _h	_	3.3 ± 0.3	1.0	ns
(Q/D1 to Q/D8 -CLR/LOAD)			5.0 ± 0.5	1.0	
Minimum hold time	t _h	_	3.3 ± 0.3	1.0	ns
(SI-CK)			5.0 ± 0.5	1.5	
Minimum removal time	t _{rem}	_	3.3 ± 0.3	5.0	ns
(CLR/LOAD-CK)			5.0 ± 0.5	3.0	



12.6. Timing Requirements (Unless otherwise specified, T_a = -40 to 125 °C, Input: t_f = 1 ns)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Limit	Unit
Minimum pulse width	$t_{w(L)}, t_{w(H)}$	_	3.3 ± 0.3	8.0	ns
(CK)			5.0 ± 0.5	6.0	
Minimum pulse width	t _{w(L)}	_	3.3 ± 0.3	7.0	ns
(CLR/LOAD)			5.0 ± 0.5	6.0	
Minimum setup time	t _S	_	3.3 ± 0.3	8.0	ns
(Q/D1 to Q/D8 -CLR/LOAD)			5.0 ± 0.5	7.0	
Minimum setup time	t _S	_	3.3 ± 0.3	8.0	ns
(SI-CK)			5.0 ± 0.5	5.0	
Minimum hold time	t _h	_	3.3 ± 0.3	1.0	ns
(Q/D1 to Q/D8 -CLR/LOAD)			5.0 ± 0.5	1.0	
Minimum hold time	t _h	_	3.3 ± 0.3	1.0	ns
(SI-CK)			5.0 ± 0.5	1.5	
Minimum removal time	t _{rem}	_	3.3 ± 0.3	5.0	ns
(CLR/LOAD-CK)			5.0 ± 0.5	3.0	

Rev.2.0



12.7. AC Characteristics (Unless otherwise specified, $T_a = 25$ °C, Input: $t_r = t_f = 3$ ns)

Characteristics	Symbol	Note	Test Condition	V _{CC} (V)	C _L (pF)	Min	Тур.	Max	Unit
Propagation delay time	t _{PLH} ,t _{PHL}		_	3.3 ± 0.3	15	_	9.3	14.7	ns
(CK-Q/D1 to Q/D8)					50	_	12.1	19.0	
				5.0 ± 0.5	15	_	6.7	9.7	
					50	_	9.1	13.1	
Propagation delay time	t _{PLH} ,t _{PHL}		_	3.3 ± 0.3	15	_	9.0	14.4	ns
(CK-Q8',Q8C)					50	_	11.8	18.6	
				5.0 ± 0.5	15	_	6.4	9.4	
					50	_	8.7	12.7	
Propagation delay time	t _{PLH} ,t _{PHL}		_	3.3 ± 0.3	15	_	7.9	11.7	ns
(CLR/LOAD-Q/D1 to Q/D8)					50	_	10.2	15.1	
				5.0 ± 0.5	15	_	6.2	8.4	
					50	_	8.0	11.1	
Propagation delay time	t _{PLH} ,t _{PHL}		_	3.3 ± 0.3	15	_	8.0	11.8	ns
(CLR/LOAD-Q8',Q8C)					50	_	10.3	15.3	
				5.0 ± 0.5	15	_	6.2	8.5	
					50	_	8.1	11.2	
Propagation delay time	t _{PLH} ,t _{PHL}		_	3.3 ± 0.3	15	_	9.5	15.2	ns
(Q/D8-Q8')					50	_	11.8	18.9	
				5.0 ± 0.5	15	_	6.7	9.6	
					50	_	8.4	12.2	
3-state output enable time	t_{PZL}, t_{PZH}		$R_L = 1 k\Omega$	3.3 ± 0.3	15	_	6.7	10.4	ns
(P/S CONT-Q/D1 to Q/D8)					50	_	9.9	15.4	
				5.0 ± 0.5	15	_	5.0	7.3	
					50	_	7.6	11.0	
3-state output disable time	t_{PLZ}, t_{PHZ}		$R_L = 1 k\Omega$	3.3 ± 0.3	50	_	10.1	12.8	ns
(P/S CONT-Q/D1 to Q/D8)				5.0 ± 0.5	50	_	7.8	9.8	
Maximum clock frequency	f _{MAX}		_	3.3 ± 0.3	15	68	107	_	MHz
					50	52	82	_	
				5.0 ± 0.5	15	103	149	_	
					50	76	109	_	
Input capacitance	C _{IN}		_		'	_	4	10	pF
Bus I/O capacitance	C _{I/O}		Q/D1 to Q/D8			_	8	_	pF
Power dissipation capacitance	C _{PD}	(Note 1)	P/S CONT = L (Parallel Outputs)			_	102	_	pF
			P/S CONT = H (Parallel Inputs)			_	34	_	

Note 1: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation. $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}$



12.8. AC Characteristics (Unless otherwise specified, T_a = -40 to 85 °C, Input: t_r = t_f = 3 ns)

Characteristics	Symbol	Test Condition	V _{CC} (V)	C _L (pF)	Min	Max	Unit
Propagation delay time	t _{PLH} ,t _{PHL}	_	3.3 ± 0.3	15	1.0	16.7	ns
(CK-Q/D1 to Q/D8)				50	1.0	21.6	
			5.0 ± 0.5	15	1.0	11.1	
				50	1.0	14.9	
Propagation delay time	t _{PLH} ,t _{PHL}	_	3.3 ± 0.3	15	1.0	16.4	ns
(CK-Q8',Q8C)				50	1.0	21.2	
			5.0 ± 0.5	15	1.0	10.7	
				50	1.0	14.5	
Propagation delay time	t _{PLH} ,t _{PHL}	_	3.3 ± 0.3	15	1.0	13.4	ns
(CLR/LOAD-Q/D1 to Q/D8)				50	1.0	17.2	
			5.0 ± 0.5	15	1.0	9.6	
				50	1.0	12.6	
Propagation delay time	t _{PLH} ,t _{PHL}	_	3.3 ± 0.3	15	1.0	13.5	ns
(CLR/LOAD-Q8',Q8C)				50	1.0	17.5	
			5.0 ± 0.5	15	1.0	9.7]
				50	1.0	12.8	
Propagation delay time	t _{PLH} ,t _{PHL}	_	3.3 ± 0.3	15	1.0	17.3	ns
(Q/D8-Q8')				50	1.0	21.6	j i
			5.0 ± 0.5	15	1.0	10.9	
				50	1.0	13.9	
3-state output enable time	t _{PZL} ,t _{PZH}	$R_L = 1 k\Omega$	3.3 ± 0.3	15	1.0	11.9	ns
(P/S CONT-Q/D1 to Q/D8)				50	1.0	17.6	
			5.0 ± 0.5	15	1.0	8.3	
				50	1.0	12.5	
3-state output disable time	t _{PLZ} ,t _{PHZ}	$R_L = 1 k\Omega$	3.3 ± 0.3	50	1.0	13.7	ns
(P/S CONT-Q/D1 to Q/D8)			5.0 ± 0.5	50	1.0	10.6	
Maximum clock frequency	f _{MAX}		3.3 ± 0.3	15	59	_	MHz
				50	46	_	
			5.0 ± 0.5	15	90	_	
				50	67	_	
Input capacitance	C _{IN}					10	pF



12.9. AC Characteristics (Unless otherwise specified, T_a = -40 to 125 °C, Input: t_r = t_f = 3 ns)

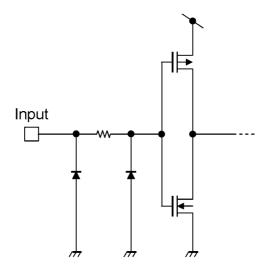
Characteristics	Symbol	Test Condition	V _{CC} (V)	C _L (pF)	Min	Max	Unit
Propagation delay time	t _{PLH} ,t _{PHL}	_	3.3 ± 0.3	15	1.0	18.5	ns
(CK-Q/D1 to Q/D8)				50	1.0	23.5	
			5.0 ± 0.5	15	1.0	12.5]
				50	1.0	16.5	
Propagation delay time	t _{PLH} ,t _{PHL}	_	3.3 ± 0.3	15	1.0	18.0	ns
(CK-Q8',Q8C)				50	1.0	23.0	
			5.0 ± 0.5	15	1.0	12.0]
				50	1.0	16.0]
Propagation delay time	t _{PLH} ,t _{PHL}	_	3.3 ± 0.3	15	1.0	15.0	ns
(CLR/LOAD-Q/D1 to Q/D8)				50	1.0	19.0	1
			5.0 ± 0.5	15	1.0	10.5	1
				50	1.0	14.0	1
Propagation delay time	t _{PLH} ,t _{PHL}	_	3.3 ± 0.3	15	1.0	15.0	ns
(CLR/LOAD-Q8',Q8C)				50	1.0	19.0]
			5.0 ± 0.5	15	1.0	10.5	1
				50	1.0	14.0	ns
Propagation delay time	t _{PLH} ,t _{PHL}	_	3.3 ± 0.3	15	1.0	19.0	ns
(Q/D8-Q8')				50	1.0	23.5]
			5.0 ± 0.5	15	1.0	12.0]
				50	1.0	15.5]
3-state output enable time	t _{PZL} ,t _{PZH}	$R_L = 1 k\Omega$	3.3 ± 0.3	15	1.0	13.0	ns
(P/S CONT-Q/D1 to Q/D8)				50	1.0	19.5]
			5.0 ± 0.5	15	1.0	9.0]
				50	1.0	13.5]
3-state output disable time	t _{PLZ} ,t _{PHZ}	$R_L = 1 k\Omega$	3.3 ± 0.3	50	1.0	14.5	ns
(P/S CONT-Q/D1 to Q/D8)			5.0 ± 0.5	50	1.0	11.5	1
Maximum clock frequency	f _{MAX}	_	3.3 ± 0.3	15	50	_	MHz
				50	40	_	
			5.0 ± 0.5	15	80]
				50	60	_	
Input capacitance	C _{IN}	_			_	10	pF

12.10. Noise Characteristics (Unless otherwise specified, T_a = 25 °C, Input: t_f = t_f = 3 ns)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Тур.	Limit	Unit
Quiet output maximum dynamic V _{OL}	V _{OLP}	C _L = 50 pF	5.0	0.6	1.0	V
Quiet output minimum dynamic V _{OL}	V _{OLV}	C _L = 50 pF	5.0	-0.5	-1.0	V
Minimum high-level dynamic input voltage	V_{IHD}	C _L = 50 pF	5.0	_	3.5	V
Maximum low-level dynamic input voltage	V_{ILD}	C _L = 50 pF	5.0	_	1.5	V

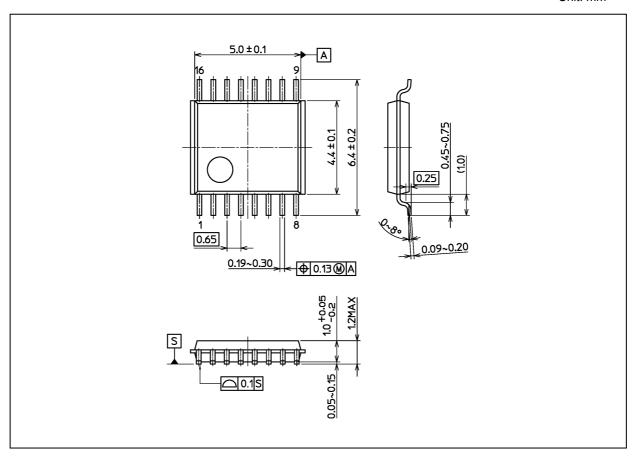


13. Internal Equivalent Circuit



Package Dimensions

Unit: mm



Weight: 0.055 g (typ.)

Package Name(s)
Nickname: TSSOP16B



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